JST20A-800CW 20A TRIAC

Rev.A.1.1

DESCRIPTION:

>>BDC /T1 1 Tf4 -0.006 1 .08 764.5 .08 365 MCID 1-27(989)-Tj e

Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D = V_{DRM} T_j =125 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	50	mA
				60	
I_H	I_T =500mA		MAX.	40	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	1600	V s
(dI/dt)c	G 9 G W F j=9125 V 7		MIN.	20	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	7	s
t_{off}				50	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX .)	Unit
V_{TM}	I_{TM} =28A t_p=380 s	T_j=25	1.4	V
V_{TO}	Threshold voltage	T_j=125	0.75	V
R_D	Dynamic resistance	T_j=125	20	P
I_{DRM}	V_D = V_{DRM} V_R = V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=125	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.9	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION

J	ST	20	A	-800	CW
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}$:20A	A:TO-220A(Ins)	800:V_{DRM} /V_{RRM} 1800 V	CW:I_{GT1-3} 035 mA

MARKING

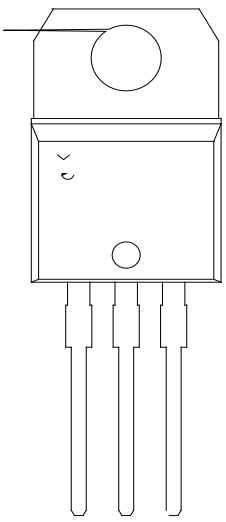


FIG.1: Maximum power dissipation versus RMS on-state current

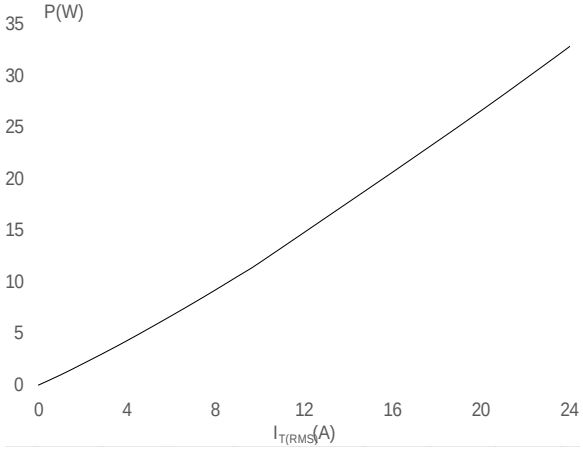


FIG.2: RMS on-state current versus case temperature

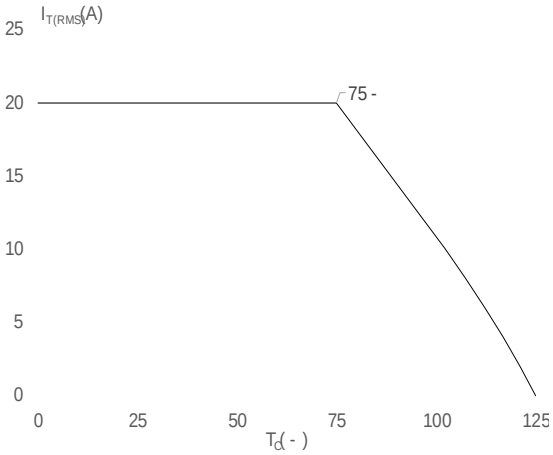


FIG.3: Surge peak on-state current versus number of cycles

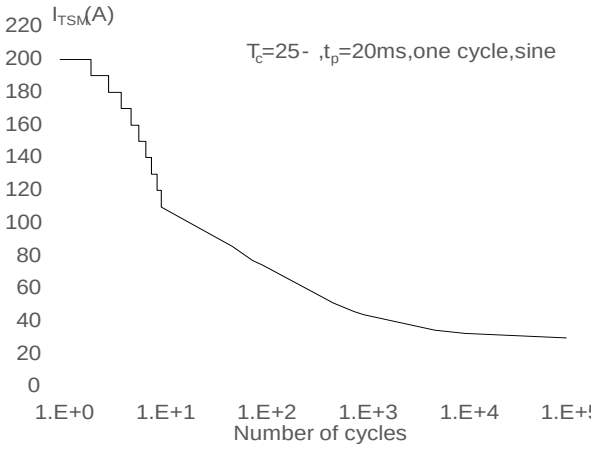
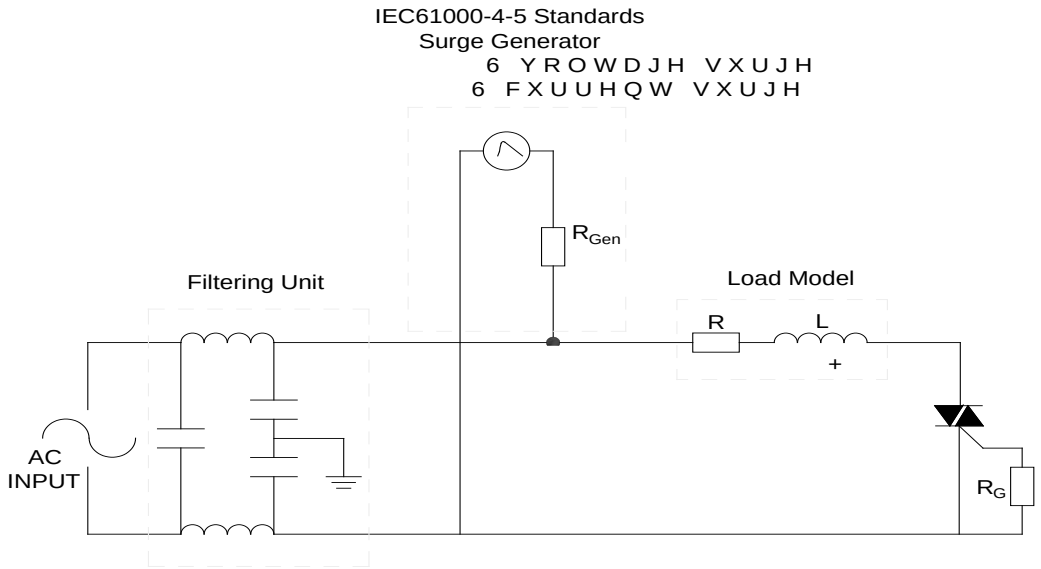


FIG.4: On-state characteristics

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



PACKAGE MECHANICAL DATA